

IFW

CS-03-028



June 14, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
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Subject: | Serial No. 10/828,887 04/21/04 |

Yisuo Li et al.

SHALLOW LOW ENERGY ION IMPLANTATION
INTO PAD OXIDE FOR IMPROVING
THRESHOLD VOLTAGE STABILITY

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
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P.O. Box 1450, Alexandria, VA 22313-1450, on June 17, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 6/17/04

U.S. Patent 4,154,626 to Joy et al., "Process of Making Field Effect Transistor Having Improved Threshold Stability by Ion-Implantation," describes a process of making an FET device with improved threshold stability by ion implantation.

U.S. Patent 6,177,333 to Rhodes, "Method for Making a Trench Isolation for Semiconductor Devices," describes a method for making trench isolations in semiconductor devices.

U.S. Patent Application Publication US 2002/0179997 A1 to Goth et al., "Self-Aligned Corner Vt Enhancement with Isolation Channel Stop by Ion Implantation," describes a process of fabricating an FET device using a simultaneous implantation of the well species at the edge of the device and at the bottom of the shallow trench isolation regions.

U.S. Patent Application Publication US 2001/0021545 A1 to Houlihan et al., "Method for Eliminating Transfer Gate Sacrificial Oxide," describes a method for eliminating the transfer gate sacrificial oxide.

Sincerely,



Stephen B. Ackerman,
Reg. No. 37761

**INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**

JUN 21 2004

(Use several sheets if necessary)

DocId Number (Optional)

CS-03-028

Application Number

10/828,887

Applicant

Yisuo Li et al.

Filing Date

04/21/04

Group Art Unit

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
4154626	5/15/79	Joy et al.	148	1.5	2/24/78
6177333	1/23/01	Rhodes	438	433	1/14/99

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

- US Patent App. Pub. US 2002/0179997 A1 to Goh et al., Pub. Date 12/05/02, Filed 06/05/01, US Class 257/514.
- US Patent App. Pub. US 2001/0021545 A1 to Houlihan et al., Pub. Date 09/13/01, Filed 10/14/98, US Class 438/199.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.